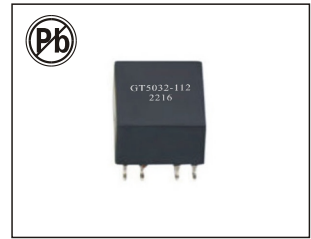


GATE DRIVE TRANSFORMERS FOR IGBT

GT5032 Series

FEATURES:

- Low coupling capacitance
- High insulation strength (reinforced insulation)
- Very high corona extinction voltage
- Compact designs in THT and SMT casings



DESCRIPTION:

In modern variable-frequency drives (VFD) IGBT are used in the inverter stage for frequency conversion. The corresponding Gate Driver Circuit needs to supply the necessary power for switching. In medium to high power applications DC/DC converters are usually used for this purpose.

Gate Drive Transformers for IGBT are the key element in these converters maintaining the safe galvanic separation between the intermediate circuit and the low voltage control side.

By using toroidal cores made from nanocrystalline it is possible to transmit the required switching power in extremely compact casings saving valuable PCB space. Advanced insulation and winding concepts ensure highest corona extinction voltages as well as low coupling capacitances.

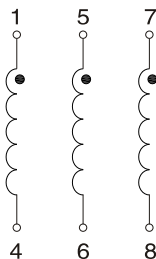
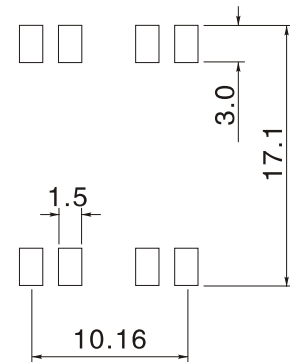
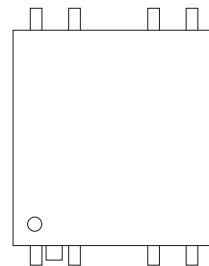
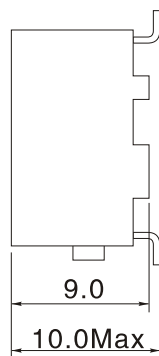
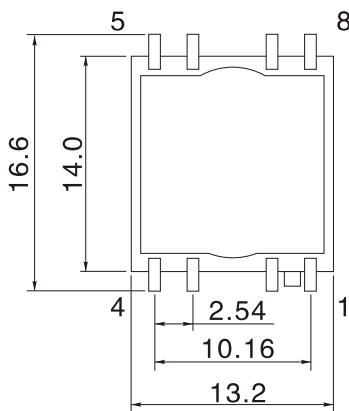
A large portfolio for typical working voltages between 500 V and 1200 V is available. The transformers feature different transmission ratios and voltage-time areas for demanding applications.

STANDARD SPECIFICATION:

Part Number	Turns ratio	Operating frequency (KHz)	Transmittable power (W)	Pri. Inductance (mH)Min @10KHz	Pri. Leakage inductance (Short Sec.) (uH)Typ. @100KHz	Capacitance Pri to Sec (pF)Typ.	Max Working Voltage (V)	Hi-Pot (kV)
GT5032-112	1:1:1	80	5	0.7	2.8	3.8	300	5.0

PHYSICAL CHARACTERISTICS

TECHNICAL INFORMATION:



Notes:

Electrical specification at 25°C

Operating temperature range: -40°C to +105°C

Storage temperature range: -40°C to +105°C